

**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

**LISTING OF CLAIMS:**

1. (currently amended): A method of forming an oxide film, comprising the steps of:
  - (a) starting a supply of a reaction gas at a first flow rate into a chamber in which a plasma is formed, such that an initial film is formed on a center region of a wafer via a first nozzle provided on the chamber above the center region of the wafer; and
  - (b) starting a supply of the reaction gas at a second flow rate into the chamber in which the plasma is formed via second nozzles, wherein said second nozzles are provided on side walls of the chamber above the wafer, after said step (a), while the supply of the reaction gas at said first flow rate continues such that the oxide film is formed on the initial film, the first flow rate being smaller than the second flow rate,  
  
wherein the formation of said oxide film is initiated from the center region of the wafer in the above step (a), and said oxide film is formed on the whole of the wafer in step (b); and wherein said step (b) is carried out 1 to 10 seconds after said step (a) is carried out.
2. (original): The method according to claim 1, wherein said reaction gas is a compound gas containing Si.

3. (original): The method according to claim 2, wherein said reaction gas is one of  $\text{SiH}_4$ ,  $\text{SiF}_4$  and TEOS.

4. (canceled).

5. (original): The method according to claim 1, wherein said first flow rate is in a range of one fifth to one tenth of said second flow rate.

6. (canceled).

7. (canceled).

8. (currently amended): A method of forming an oxide film, comprising the steps of:

(a) forming an initial film from a center region of a wafer by supplying a reaction gas at a first flow rate, via a first nozzle, wherein said first nozzle is provided on the chamber above a center region of the wafer, while a thickness of the film is equal to or thinner than 10 nm; and

(b) forming the oxide film on said wafer, by starting to supply the reaction gas at a second flow rate, via second nozzles, wherein said second nozzles are provided on side walls of the chamber above the wafer, after said step (a), while continuing to supply the reaction gas at said first flow rate,

wherein the formation of said oxide film is initiated from the center region of the wafer in the above step (a), and said oxide film is formed on the whole of the wafer in step (b); and wherein said step (b) is carried out 1 to 10 seconds after said step (a) is carried out.

9. (previously presented): The method according to claim 8, wherein said first flow rate is in a range of one fifth to one tenth of said second flow rate.

10. (original): The method according to claim 8, wherein said reaction gas is a compound gas containing Si.

11. (original): The method according to claim 10, wherein said reaction gas is one of SiH<sub>4</sub>, SiF<sub>4</sub> and TEOS.

12. (canceled).

13. (canceled).

14. (canceled).